Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	43	esd and lcd near panel and (MOS FET MOSFET field near effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:09
S3	2	"20020126430"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:13
S4	7	"6,678,133"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:13
S5	21	("5218222" | "5293057" | "5336908" | "5430602" | "5581104" | "5654860" | "5656967" | "5721658" | "5744839" | "5767552" | "5805009" | "5880917" | "5889644" | "5982599" | "6004838" | "6040733" | "6130811" | "6137664" | "6181540" | "6204537" | "RE36024"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/18 12:13
S6	1	("6678133").URPN.	USPAT	OR	ON	2005/08/18 12:22
S7	5	esd and (pad line terminal) and protect$3 near device same impedance near (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:44
S8	5	esd and protect$3 near device same impedance near (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:47
S9	45	esd and protect$3 near device same impedance near (small$3 high$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:47

S10	11	esd and protect$3 near device same impedance near3 (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 10:04
S11	11	esd and protect$3 near device same impedance near3 (smaller higher larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 10:06
S12	52	esd and protect$3 near device same (impedance resistance) near3 (smaller higher larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:12
S13	1	esd and protect$3 near device same (impedance resistance) near3 gradually near3 (increas$3 decreas$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:12
S14	18	esd and (impedance resistance) near3 gradually near3 (increas$3 decreas$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S15	18	esd and (impedance resistance) near4 gradually near3 (increas$3 decreas$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S16	18	esd and (impedance resistance) near4 gradually near4 (increas$3 decreas$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S17	36	esd and (impedance resistance) same gradually near3 (increas$3 decreas$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:08

S18	15	"6,198,136"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:13
S19	22069	(esd (electrostatic adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:14
S20	1375	S19 same impedance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:15
S21	274	S19 same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:16
S22	4	S21 same compensat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:18
S23	343	S19 same compensat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:18
S24	142	S23 same (size length dimension inductance capacitance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:19
S25	72	S23 same (size length dimension)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:53

S26	429	esd and channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:53
S27	133	esd and channel near width same (impedance resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:54
S28	1	esd and channel near width same (impedance resistance) same gradually	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:54
S29	30	esd and channel near width same (impedance resistance) same (increase decrease)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 16:37
S30	608	361/91.1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 16:37
S31	224	esd and (lead wire) near (impedance resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:27
S32	0	esd and (lead wire) near (impedance resistance) near compensat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:28
S33	7	esd and (lead wire) near (impedance resistance) near (compensat$5 chang$3 modificat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:31

S34	9	esd and (lead wire connect$3) near (impedance resistance) near (compensat$5 chang$3 modificat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:33
S35	13	esd and (lead wire connect$3) near3 (impedance resistance) near (compensat$5 chang$3 modificat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:34
S36	35	esd and (lead wire connect$3) near3 (impedance resistance) near (match$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 10:18
S37	3	("4455586" | "4930644" | "5416660"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 09:46
S38	0	("6847511").URPN.	USPAT	OR	ON	2005/11/16 09:49
S39	8	esd and (lead wire connect$3) near3 (impedance resistance) near (match$5) and channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:24
S40	23	esd and (lead wire connect$3) with (impedance resistance) with (match$5) and channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18
S41	145	esd and lcd near panel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:18
S42	7	esd and (lead wire trace) with (impedance resistance) with (match$5) and channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:19
S43	4	("4719369" | "5602494" | "6366129" | "6642740").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 14:36

S44	2383	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18
S45	1377	(esd (electrostatic adj discharge)) same impedance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 09:18
S46	175	(esd (electrostatic adj discharge)) same impedance same (size length dimension)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 09:18
S47	22	(esd (electrostatic adj discharge)) same impedance same (size length dimension) with (lead wire trace)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:24
S48	1745	361/111.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:25
S49	1668	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 12:06